



Advanced Power
Electronics Corp.

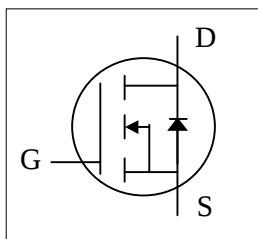
AP20T03GH/J-HF

Halogen-Free Product

N-CHANNEL ENHANCEMENT MODE

POWER MOSFET

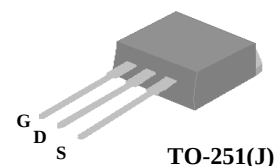
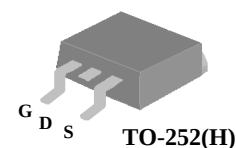
- ▼ Lower Gate Charge
- ▼ Simple Drive Requirement
- ▼ Fast Switching Characteristic
- ▼ RoHS Compliant



BV_{DSS}	30V
$R_{DS(ON)}$	50m Ω
I_D	12.5A

Description

The TO-252 package is widely preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters. The through-hole version (AP20T03GJ) is available for low-profile applications.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current	12.5	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current	8	A
I_{DM}	Pulsed Drain Current ¹	40	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation	12.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Maximum Thermal Resistance, Junction-case	10	$^{\circ}C/W$
Rthj-a	Maximum Thermal Resistance, Junction-ambient (PCB mount) ³	62.5	$^{\circ}C/W$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	110	$^{\circ}C/W$

Data & specifications subject to change without notice

1

200903204



AP20T03GH/J-HF

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =8A	-	-	50	mΩ
		V _{GS} =4.5V, I _D =5A	-	-	80	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	-	3	V
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =5A	-	6	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =30V, V _{GS} =0V	-	-	1	uA
	Drain-Source Leakage Current (T _j =125°C)	V _{DS} =24V, V _{GS} =0V	-	-	250	uA
I _{GSS}	Gate-Source Leakage	V _{GS} = ±20V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =10A	-	4	7	nC
Q _{gs}	Gate-Source Charge	V _{DS} =24V	-	1.5	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =4.5V	-	2.3	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =15V	-	6	-	ns
t _r	Rise Time	I _D =10A	-	30	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω, V _{GS} =10V	-	10	-	ns
t _f	Fall Time	R _D =1.5Ω	-	3	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	270	430	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	70	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	50	-	pF
R _g	Gate Resistance	f=1.0MHz	-	1.6	2.4	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =5A, V _{GS} =0V	-	-	1.3	V
t _{rr}	Reverse Recovery Time ²	I _S =10A, V _{GS} =0V,	-	16	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	9	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

APEC RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN.

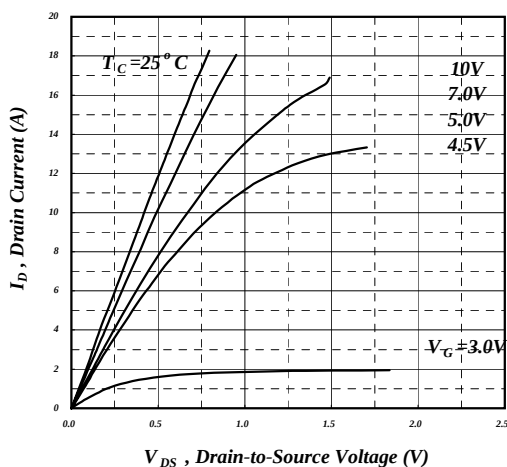


Fig 1. Typical Output Characteristics

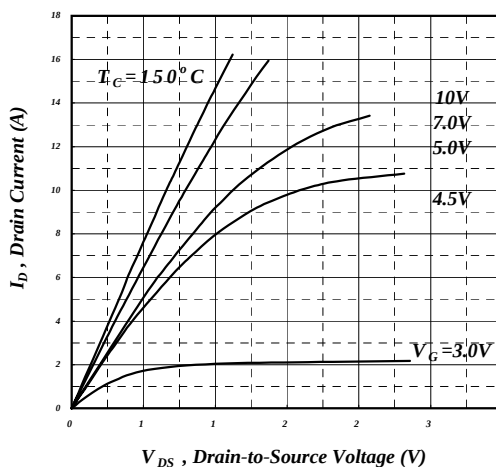


Fig 2. Typical Output Characteristics

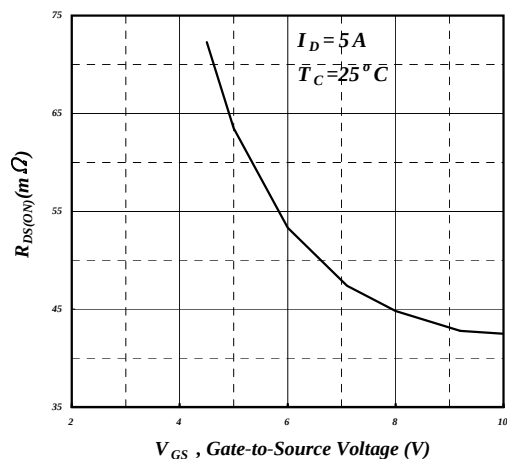


Fig 3. On-Resistance v.s. Gate Voltage

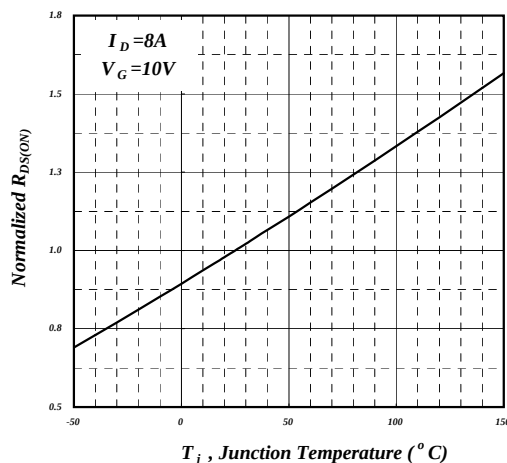


Fig 4. Normalized On-Resistance v.s. Junction Temperature

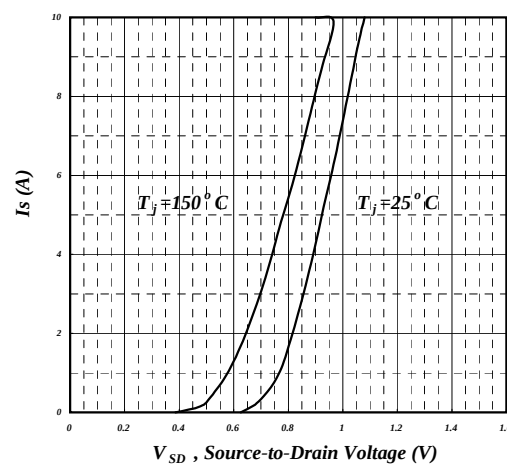


Fig 5. Forward Characteristic of Reverse Diode

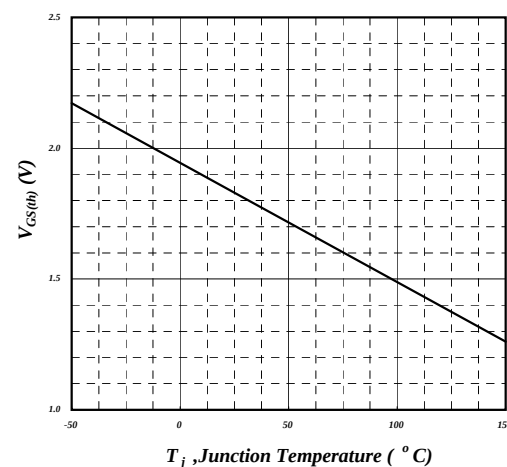


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



AP20T03GH/J-HF

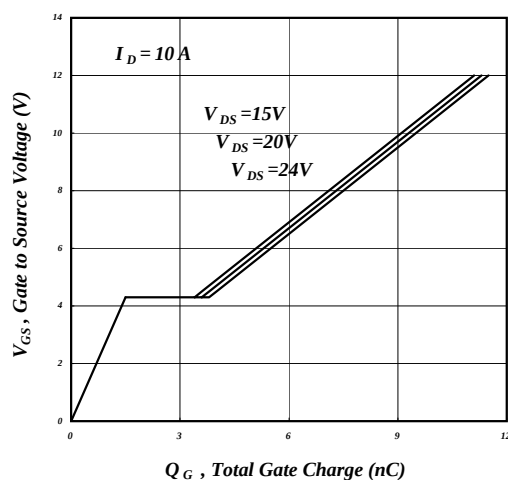


Fig 7. Gate Charge Characteristics

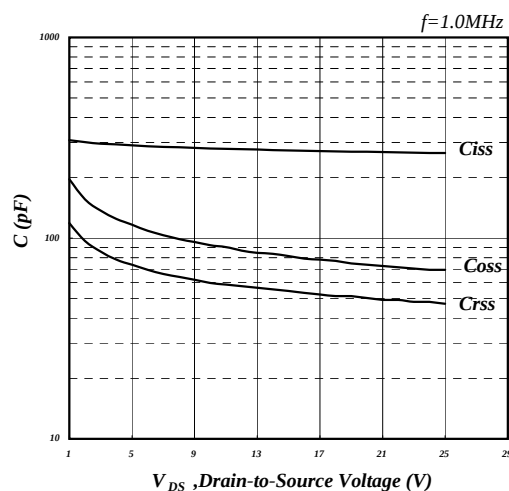


Fig 8. Typical Capacitance Characteristics

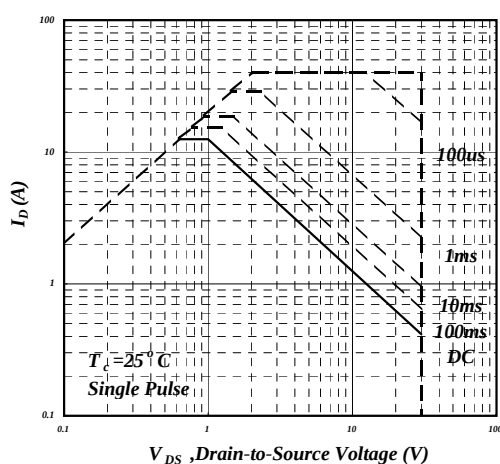


Fig 9. Maximum Safe Operating Area

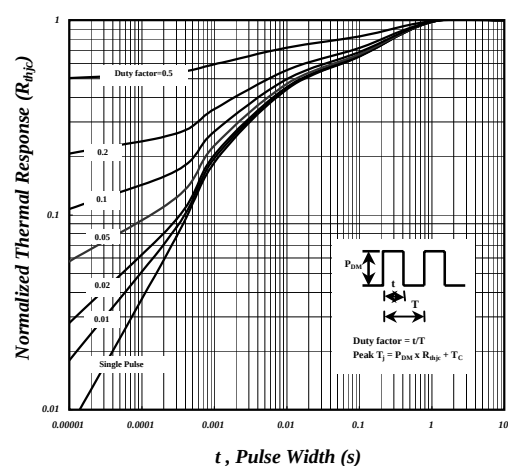


Fig 10. Effective Transient Thermal Impedance

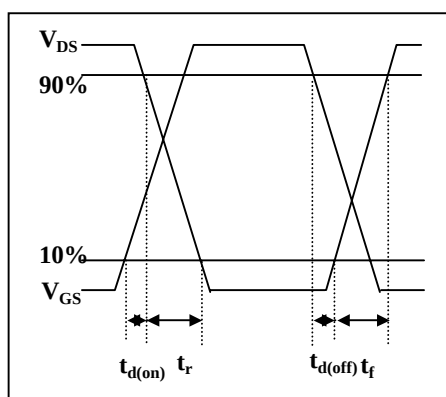


Fig 11. Switching Time Waveform

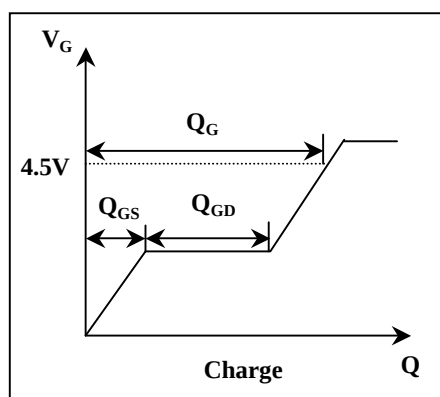


Fig 12. Gate Charge Waveform